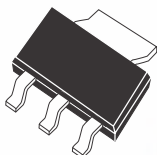


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CZT3904 NPN
CZT3906 PNP

COMPLEMENTARY
SILICON TRANSISTORS



SOT-223 CASE

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Central
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT3904, CZT3906 types are complementary silicon transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose and switching applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL	CZT3904	CZT3906	UNITS
Collector-Base Voltage	V_{CBO}	60	40	V
Collector-Emitter Voltage	V_{CEO}	40	40	V
Emitter-Base Voltage	V_{EBO}	6.0	5.0	V
Collector Current	I_C	200		mA
Power Dissipation	P_D	2.0		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150		$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	62.5		$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CZT3904		CZT3906		UNITS
		MIN	MAX	MIN	MAX	
I_{CEV}	$V_{CE}=30\text{V}, V_{EB}=3.0\text{V}$		50		50	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60		40		V
BV_{CEO}	$I_C=1.0\text{mA}$	40		40		V
BV_{EBO}	$I_E=10\mu\text{A}$	6.0		5.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.20		0.25	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.30		0.40	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$	0.65	0.85	0.65	0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.95		0.95	V
β_{FE}	$V_{CE}=1.0\text{V}, I_C=0.1\text{mA}$	40		60		
β_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{mA}$	70		80		
β_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100	300	100	300	
β_{FE}	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	60		60		
β_{FE}	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$	30		30		

SYMBOL	TEST CONDITIONS	CZT3904		CZT3906		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20V, I_C=10mA, f=100MHz$		300	250		MHz
C_{ob}	$V_{CB}=5.0V, I_E=0, f=1.0MHz$		4.0		4.5	pF
C_{ib}	$V_{BE}=0.5V, I_C=0, f=1.0MHz$		8.0		10	pF
h_{ie}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0	10	2.0	12	$k\Omega$
h_{re}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	0.5	8.0	0.1	10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	100	400	100	400	
h_{oe}	$V_{CE}=10V, I_C=1.0mA, f=1.0kHz$	1.0	40	3.0	60	$\mu mhos$
NF	$V_{CE}=5.0V, I_C=100\mu A, R_S=1.0k\Omega$ $f=10Hz$ to $15.7kHz$		5.0		4.0	dB
t_d	$V_{CC}=3.0V, V_{BE}=0.5, I_C=10mA, I_{B1}=1.0mA$		35		35	ns
t_r	$V_{CC}=3.0V, V_{BE}=0.5, I_C=10mA, I_{B1}=1.0mA$		35		35	ns
t_s	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$		200		225	ns
t_f	$V_{CC}=3.0V, I_C=10mA, I_{B1}=I_{B2}=1.0mA$		50		75	ns

All dimensions in inches (mm).

